

What is claimed:

1. A method for manufacturing an electronic device comprising a film pattern made of aluminum or a material containing aluminum as a principal component thereof, wherein, the film made of aluminum or a material containing aluminum as a principal component contains oxygen atoms at a concentration of 8×10^{18} atoms \cdot cm $^{-3}$ or less, carbon atoms at a concentration of 5×10^{18} atoms \cdot cm $^{-3}$ or less, and nitrogen atoms at a concentration of 7×10^{18} atoms \cdot cm $^{-3}$ or less; and the film pattern is subjected to a process whose process temperature is 400° or lower.

2. A method according to claim 1 further comprising the step of forming a contact hole in a silicon nitride film formed in contact with an upper plane of the film pattern.

3. A method according to claim 1 further comprising the step of forming an oxide film on a side plane of the film pattern by means of anodic oxidation.

4. A method for manufacturing an electronic device comprising the steps of:
forming a wiring comprising an oxidizable material; and
oxidizing at least a side plane of the wiring,
wherein the wiring contains oxygen atoms at a concentration of 8×10^{18} atoms \cdot cm $^{-3}$ or less, carbon atoms at a concentration of 5×10^{18} atoms \cdot cm $^{-3}$ or less, and nitrogen atoms at a concentration of 7×10^{18} atoms \cdot cm $^{-3}$ or less.

5. A method according to claim 4 wherein the oxidizing step is carried out by anodic oxidation or plasma oxidation.

6. A method according to claim 4 wherein the oxidizable material comprises aluminum or tantalum.

7. A method for manufacturing an electronic device having an active matrix, said method comprising the steps of:
forming a plurality of gate lines comprising an oxidizable material; and

oxidizing at least a side plane of each of the gate lines,

wherein the gate lines contain oxygen atoms at a concentration of 8×10^{18} atoms·cm⁻³ or less, carbon atoms at a concentration of 5×10^{18} atoms·cm⁻³ or less, and nitrogen atoms at a concentration of 7×10^{18} atoms·cm⁻³ or less.

8. A method according to claim 7 wherein the oxidizing step is carried out by anodic oxidation or plasma oxidation.

9. A method according to claim 7 wherein the oxidizable material comprises aluminum or tantalum.

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